

isc Silicon NPN Power Transistor

2SC5248

DESCRIPTION

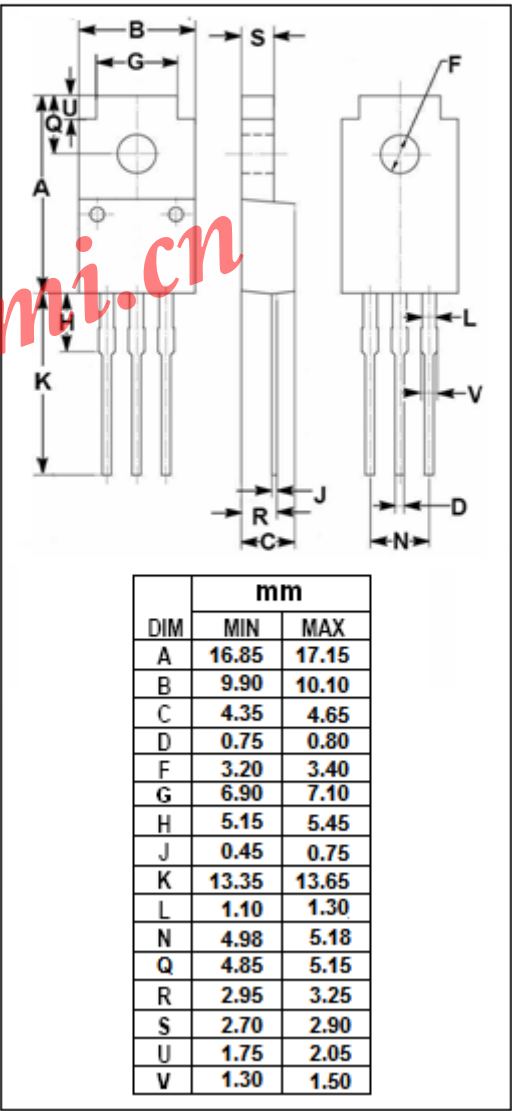
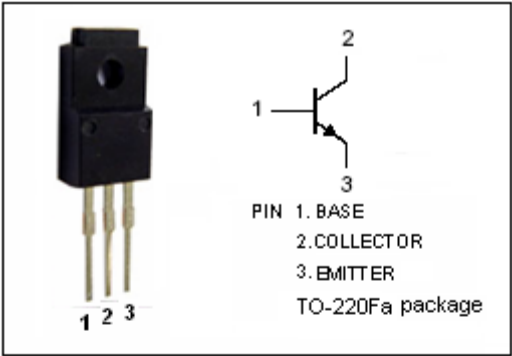
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 160V(\text{Min})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SA1964

APPLICATIONS

- Power amplifier applications.
- Driver stage amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1.5	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}C$	2	W
	Collector Power Dissipation @ $T_C=25^{\circ}C$	20	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



ISC Silicon NPN Power Transistor**2SC5248****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA; I _B = 0	160			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 50 μ A; I _E = 0	160			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 50 μ A; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1A; I _B = 0.1A			1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 160V; I _E = 0			1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			1.0	μ A
h _{FE}	DC Current Gain	I _C = 0.1A; V _{CE} = 5V	60		200	
f _T	Current-Gain—Bandwidth Product	I _C = 0.2A; V _{CE} = 10V		150		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1MHz		20		pF

◆ h_{FE} Classifications

D	E
60-120	100-200